

09788405 024501
109420 9088260

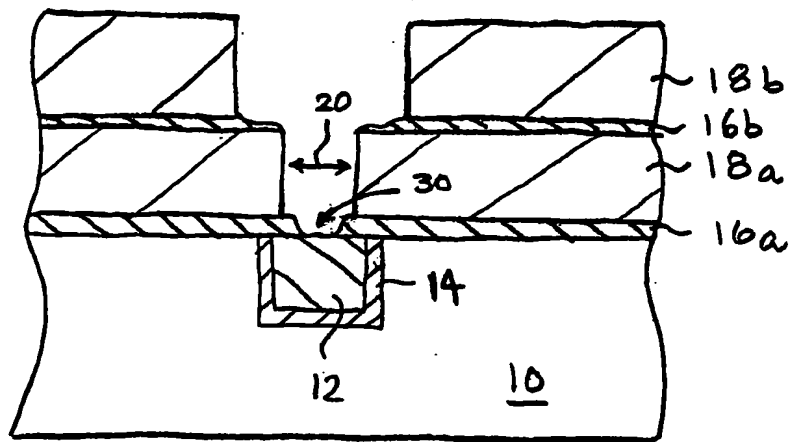


FIG. 1
(prior art)

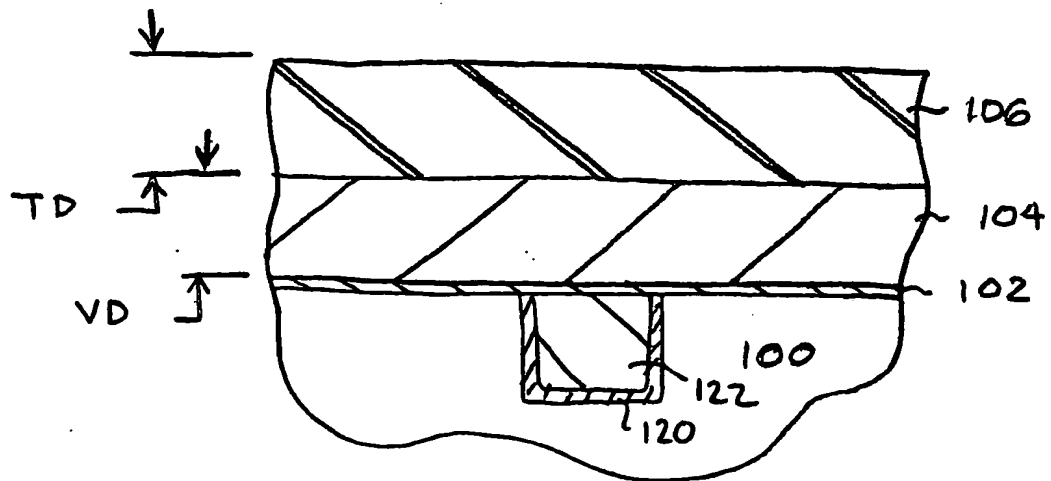


FIG. 2

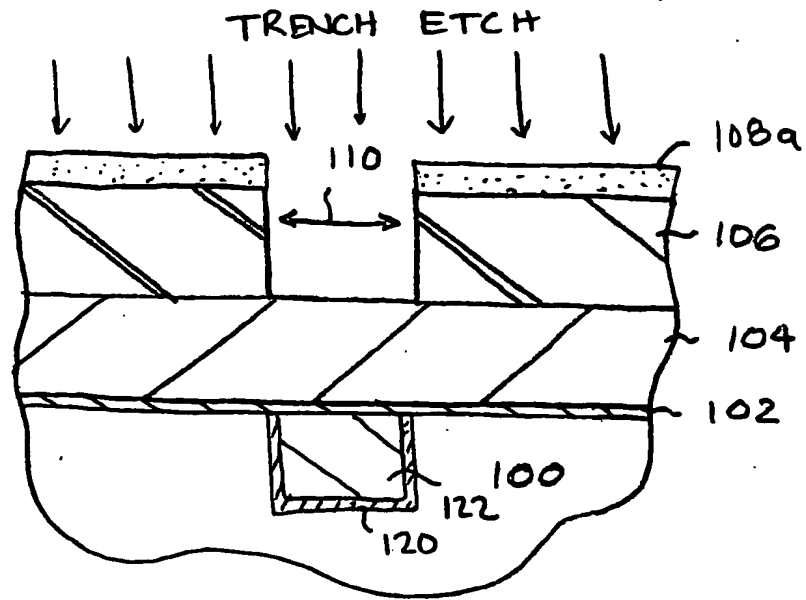


FIG. 3

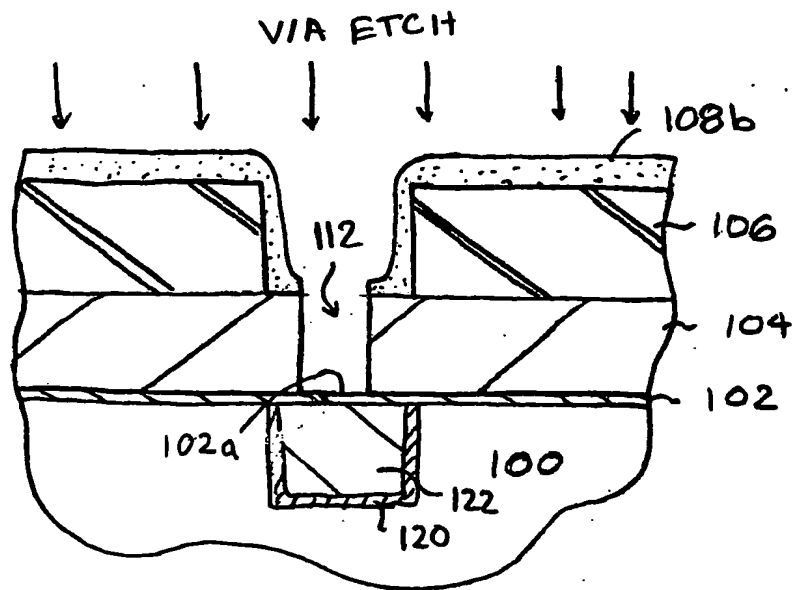


FIG. 4

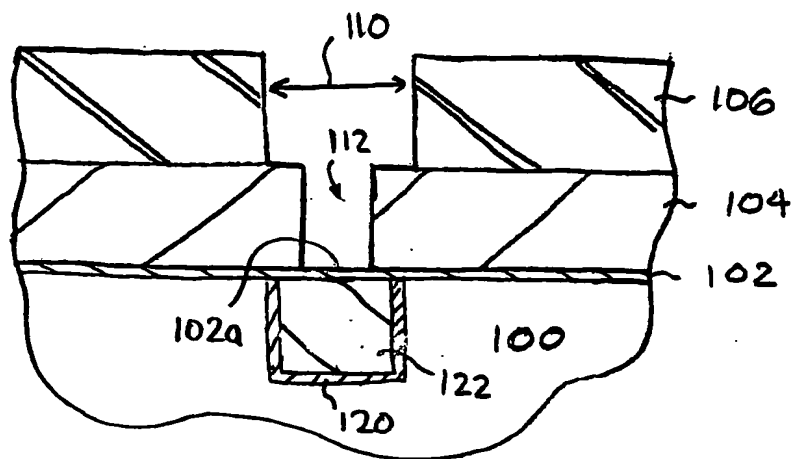


FIG. 5

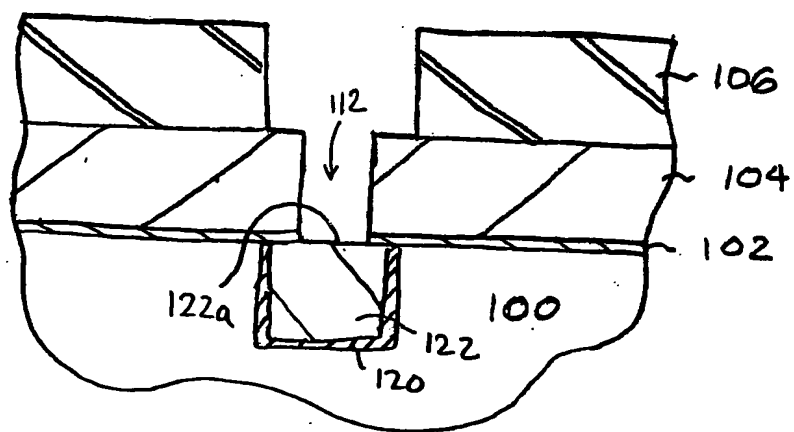


FIG. 6

TOP SECRET

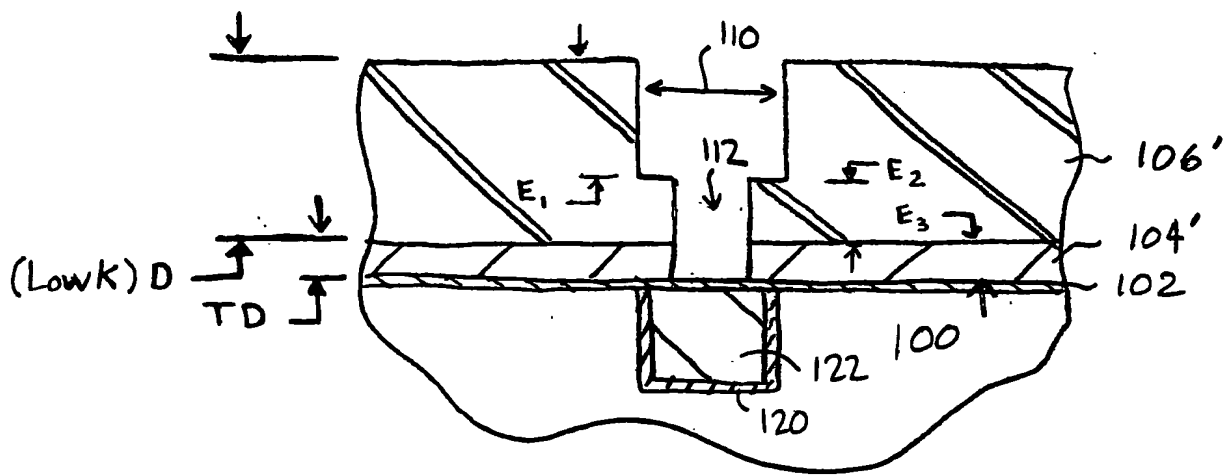


FIG. 7

A cross-sectional view of a device. A central cavity 110 is formed in a substrate 100. The cavity is defined by side walls 112 and a bottom wall 120. A layer 122 is disposed on the bottom wall 120. A top layer 204 is disposed on the side walls 112. A horizontal line 102 is shown below the cavity. To the left of the device, there are two sets of arrows: the top set is labeled 'TT' and the bottom set is labeled 'DT'.

A graph showing Carbon Content (Y-axis) versus Dielectric Thickness (X-axis). The curve is sigmoidal, starting at the origin (0,0) and leveling off at a high carbon content. Key points on the curve are labeled: 230 (near the origin), 232 (on the steep part of the curve), and 234 (on the plateau). Dashed lines indicate the carbon content 'C' on the Y-axis and the dielectric thickness 'DT' on the X-axis, corresponding to the point 234. The X-axis also has a point 'TT' marked below the curve.

FIG. 8B

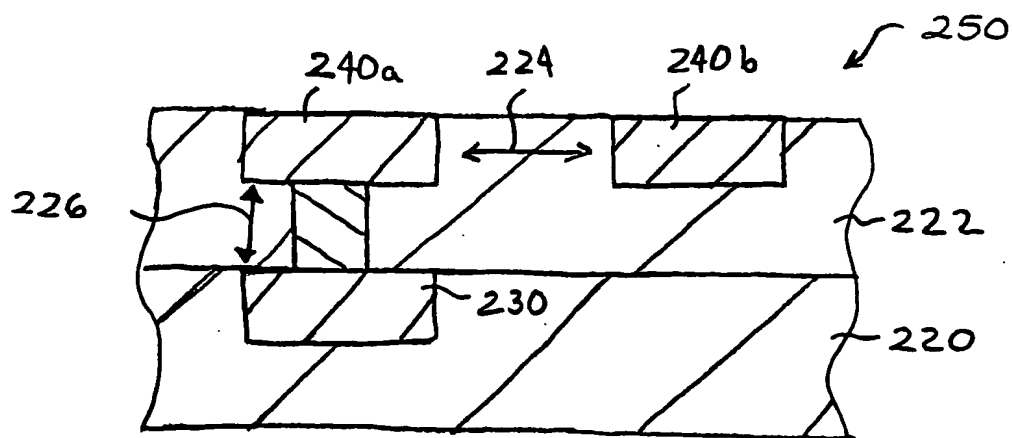


FIG. 9

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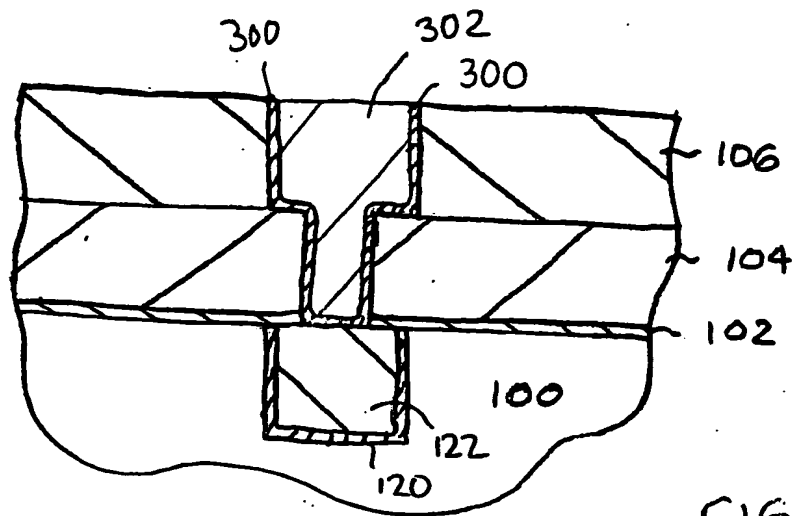


FIG. 10A

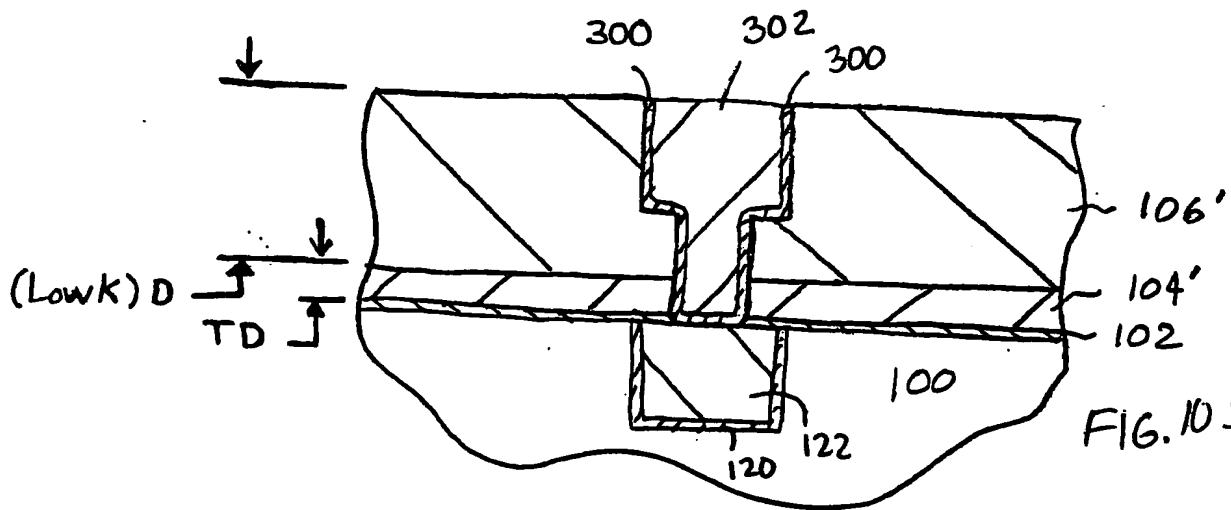


FIG. 10B

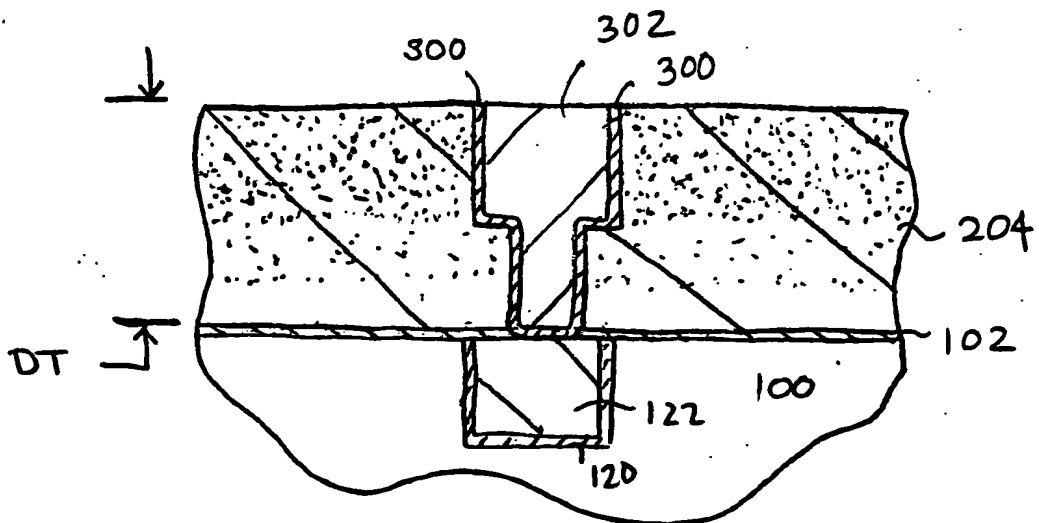


FIG. 10C

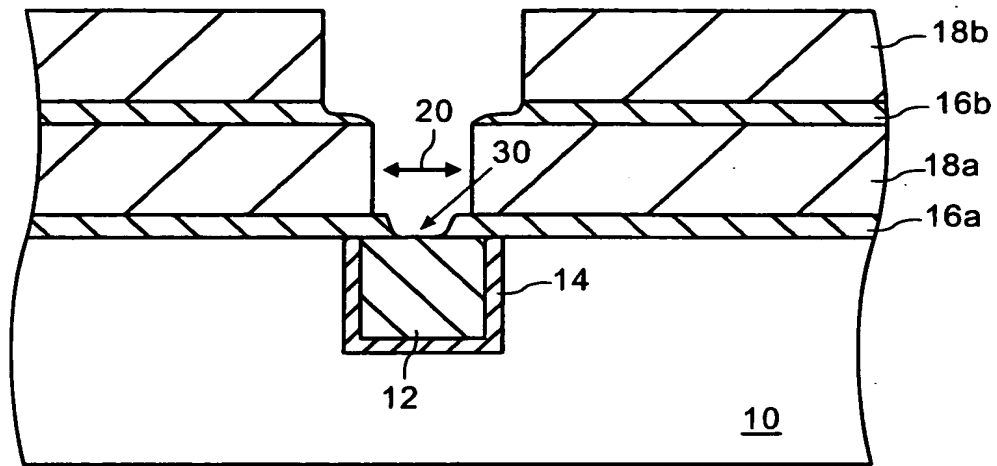


FIG. 1
(prior art)

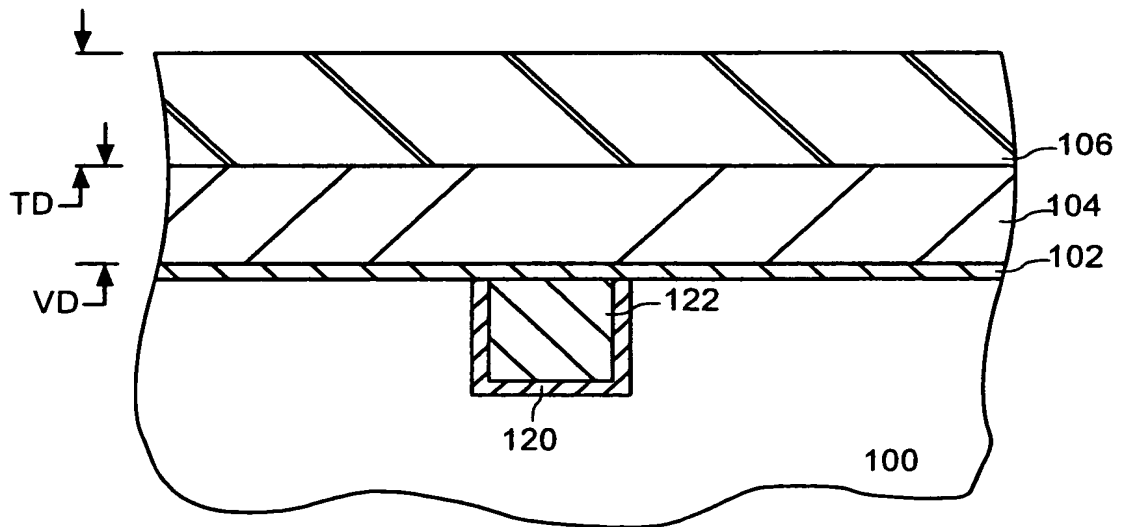


FIG. 2

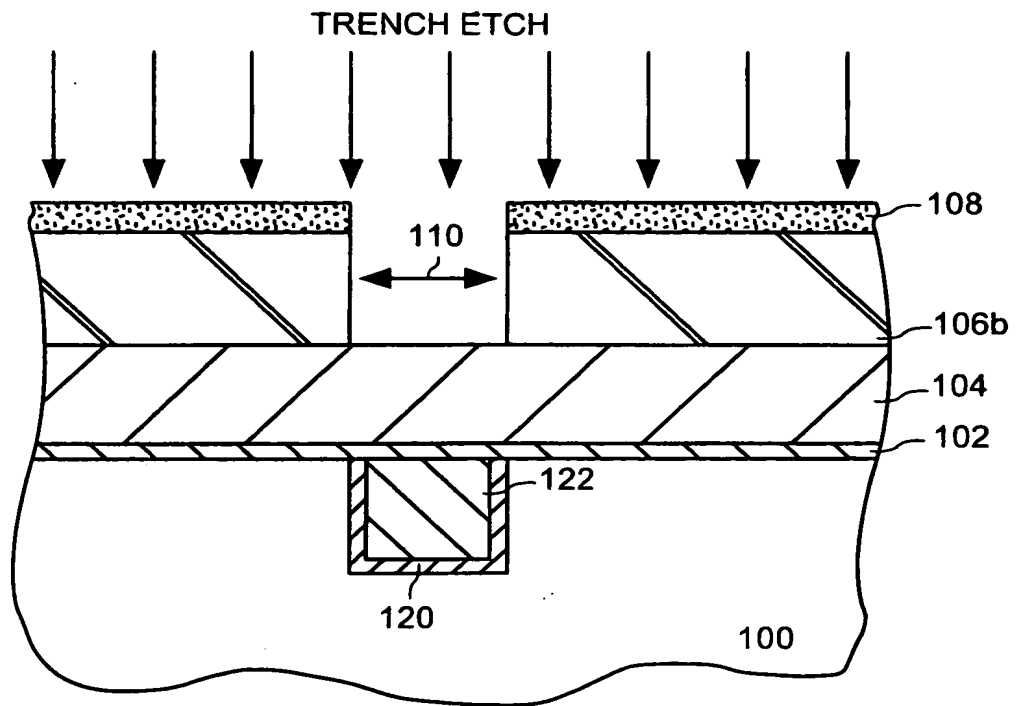


FIG. 3

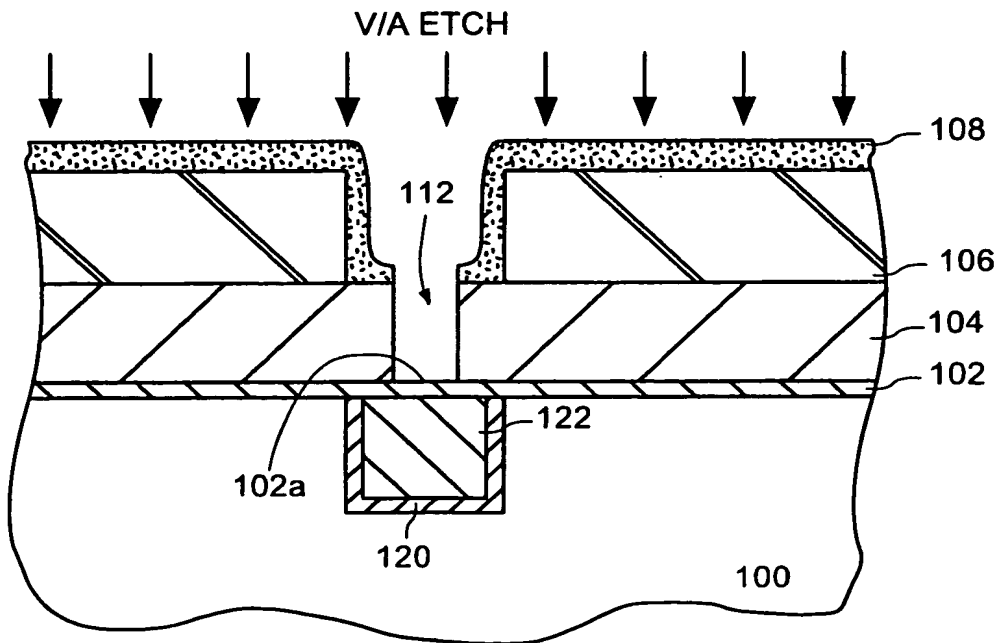


FIG. 4

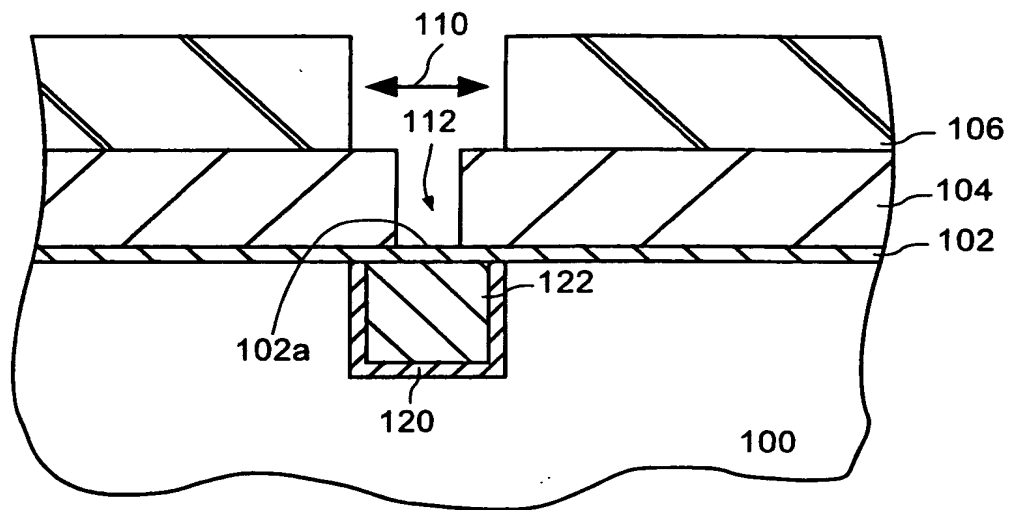


FIG. 5

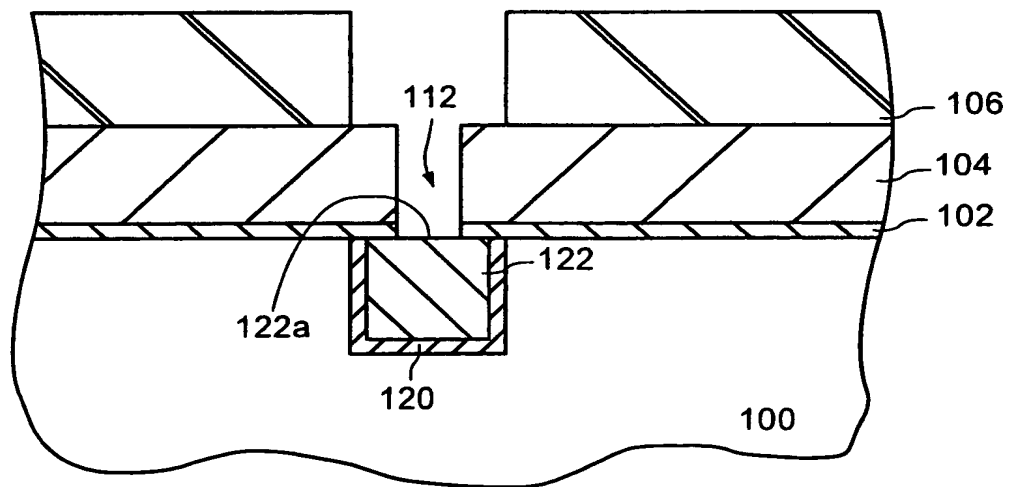


FIG. 6

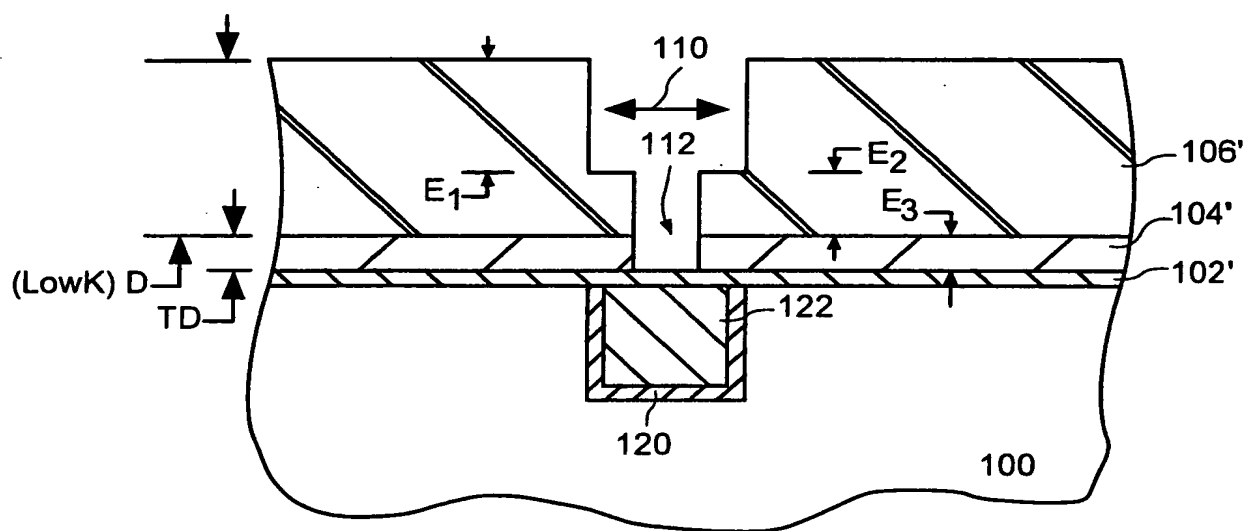


FIG. 7

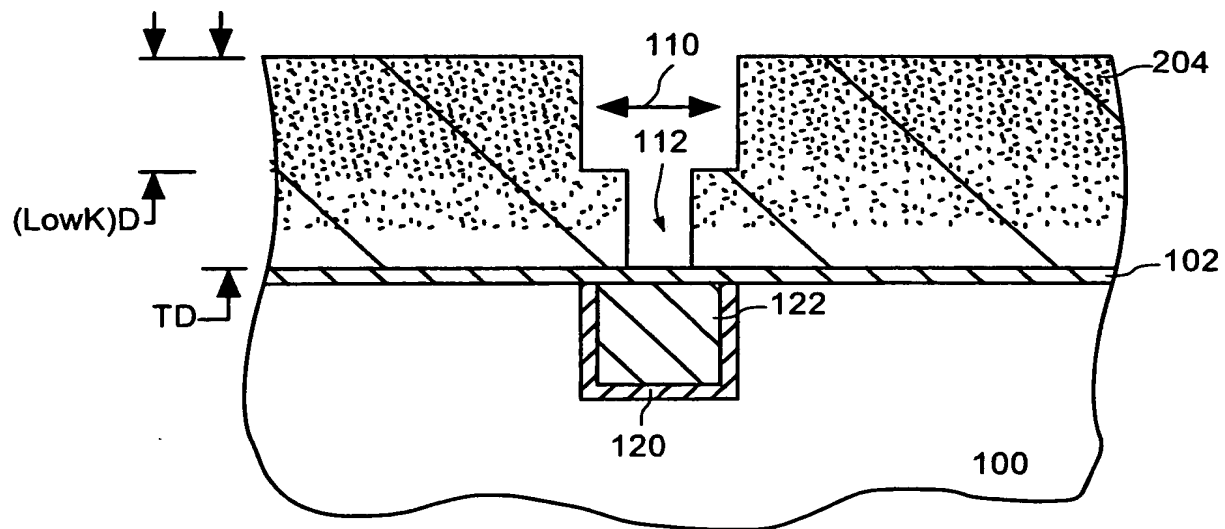


FIG. 8A

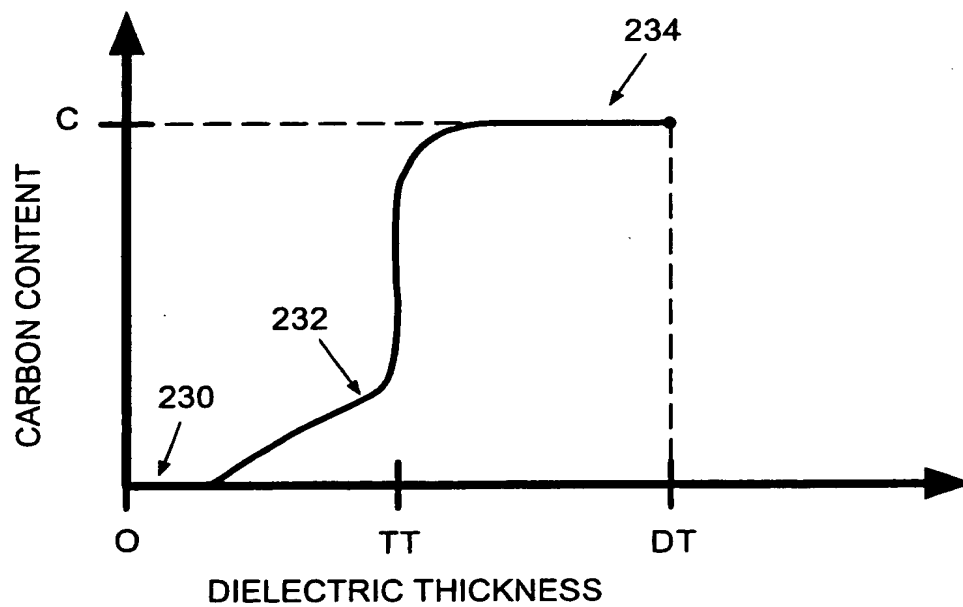


FIG. 8B

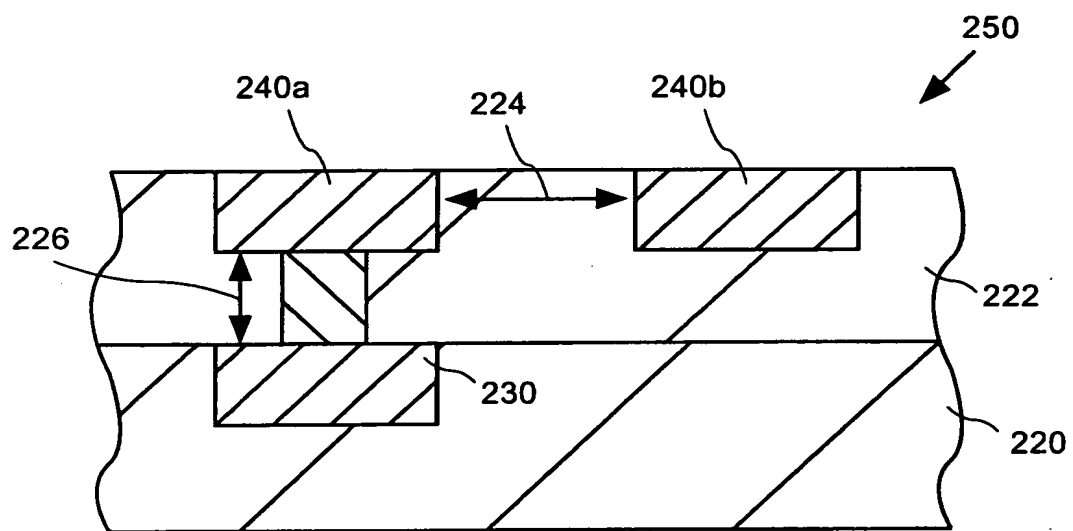


FIG. 9

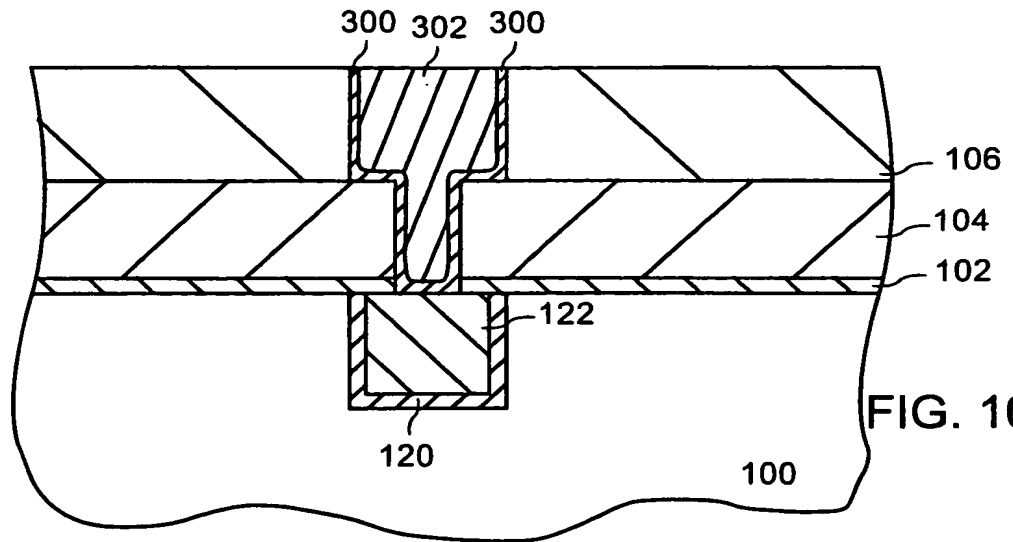


FIG. 10A

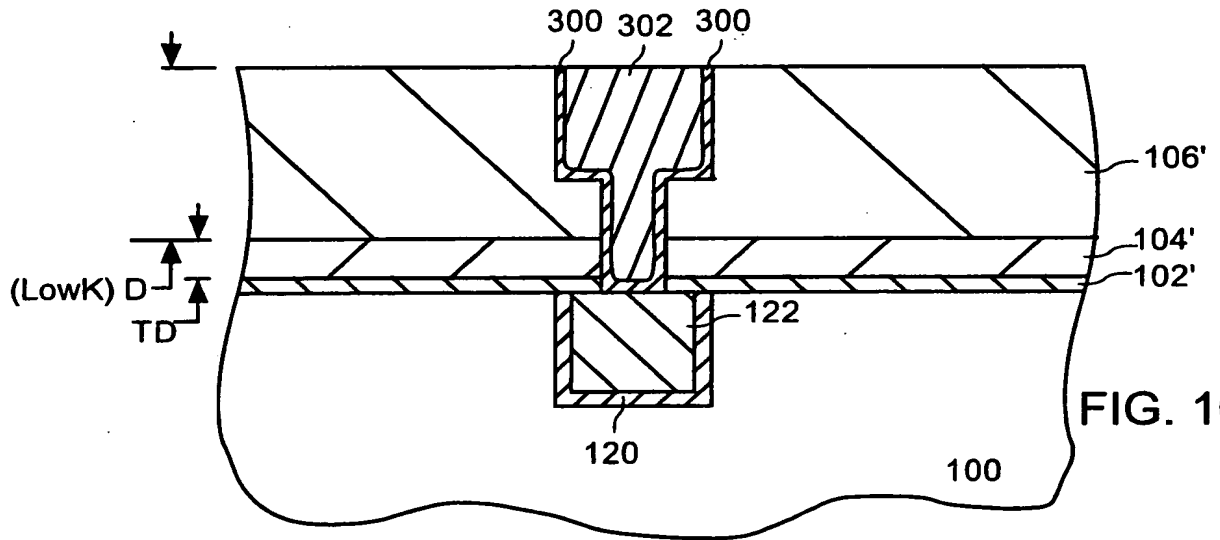


FIG. 10B

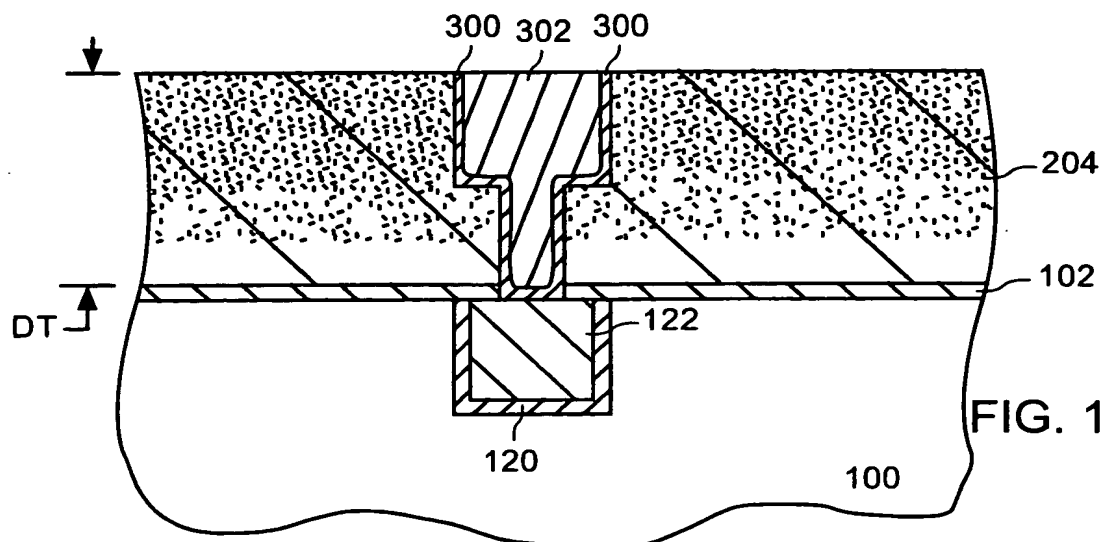


FIG. 10C